

SWITCHING REGULATOR APPLICATIONS

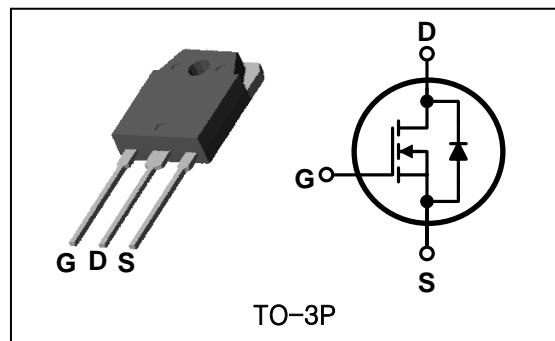
Features

- High Voltage : $BV_{DSS}=600V$ (Min.)
- Low C_{rss} : $C_{rss}=14.6pF$ (Typ.)
- Low gate charge : $Q_g=41nC$ (Typ.)
- Low $R_{DS(on)}$: $R_{DS(on)}=0.65\Omega$ (Max.)

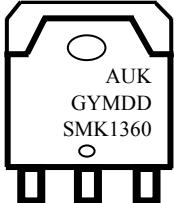
Ordering Information

Type No.	Marking	Package Code
SMK1360CI	SMK1360	TO-3P

PIN Connection



Marking Diagram

	Column 1 : Manufacturer Column 2 : Production Information e.g.) GYMDD -. G : Factory management code -. YMDD : Date Code (year, month, date)
	Column 3 : Device Code

Absolute maximum ratings ($T_c=25^\circ C$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	600	V
Gate-source voltage	V_{GSS}	± 30	V
Drain current (DC) *	I_D	($T_c=25^\circ C$) 13 ($T_c=100^\circ C$) 8.2	A
Drain current (Pulsed) *	I_{DM}	52	A
Drain power dissipation	P_D	200	W
Avalanche current (Single) ②	I_{AS}	13	A
Single pulsed avalanche energy ②	E_{AS}	544	mJ
Avalanche current (Repetitive) ①	I_{AR}	13	A
Repetitive avalanche energy ①	E_{AR}	11.6	mJ
Junction temperature	T_J	150	$^\circ C$
Storage temperature range	T_{stg}	-55~150	

* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	$R_{th(J-C)}$	-	0.625	$^\circ C/W$
	$R_{th(J-A)}$	-	40	

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0$	600	-	-	V
Gate threshold voltage	$V_{GS(\text{th})}$	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source cut-off current	I_{DSS}	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$V_{DS}=600\text{V}, V_{GS}=0\text{V}$ $T_C=125^\circ\text{C}$	-	-	100	
Gate leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm30\text{V}$	-	-	±100	nA
Drain-source on-resistance ⁽⁴⁾	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=6.5\text{A}$	-	0.55	0.65	Ω
Forward transfer conductance ⁽⁴⁾	g_{fs}	$V_{DS}=10\text{V}, I_D=6.5\text{A}$	-	10	-	S
Input capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=25\text{V},$ $f=1\text{MHz}$	-	2162	2882	pF
Output capacitance	C_{oss}		-	183	244	
Reverse transfer capacitance	C_{rss}		-	14.6	19.4	
Turn-on delay time	$t_{d(\text{on})}$	$V_{DD}=300\text{V}, I_D=13\text{A}$ $R_G=25\Omega$	-	30	-	ns
Rise time	t_r		-	85	-	
Turn-off delay time	$t_{d(\text{off})}$		-	140	-	
Fall time	t_f		-	90	-	
Total gate charge	Q_g	$V_{DS}=480\text{V}, V_{GS}=10\text{V}$ $I_D=13\text{A}$	-	41	63	nC
Gate-source charge	Q_{gs}		-	13	-	
Gate-drain charge	Q_{gd}		(3)(4)	-	10.5	-

Source-Drain Diode Ratings and Characteristics ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I_S	Integral reverse diode in the MOSFET	-	-	13	A
Source current (Pulsed) ⁽¹⁾	I_{SP}		-	-	52	
Forward voltage ⁽⁴⁾	V_{SD}	$V_{GS}=0\text{V}, I_S=13\text{A}$	-	-	1.4	V
Reverse recovery time	t_{rr}	$I_S=13\text{A}, V_{GS}=0\text{V}$ $dI_S/dt=100\text{A}/\mu\text{s}$	-	510	-	ns
Reverse recovery charge	Q_{rr}		-	4.3	-	μC

Note :

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② $L=5.9\text{mH}, I_{AS}=13\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$
- ③ Pulse Test : Pulse width $\leq 300\text{us}$, Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 I_D - V_{DS}

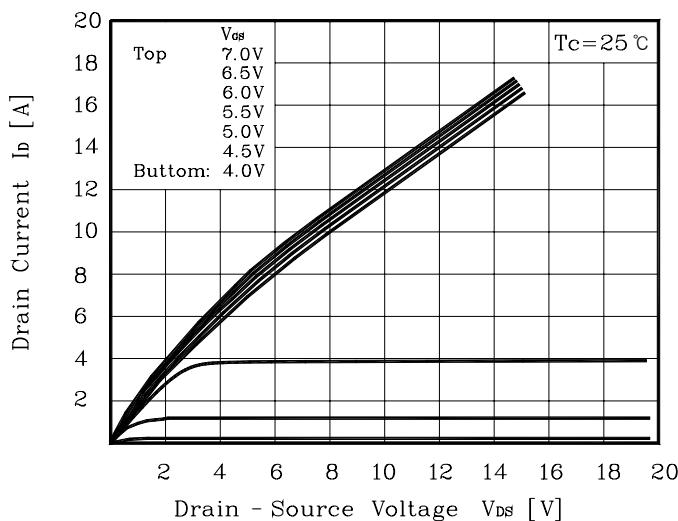


Fig. 2 I_D - V_{GS}

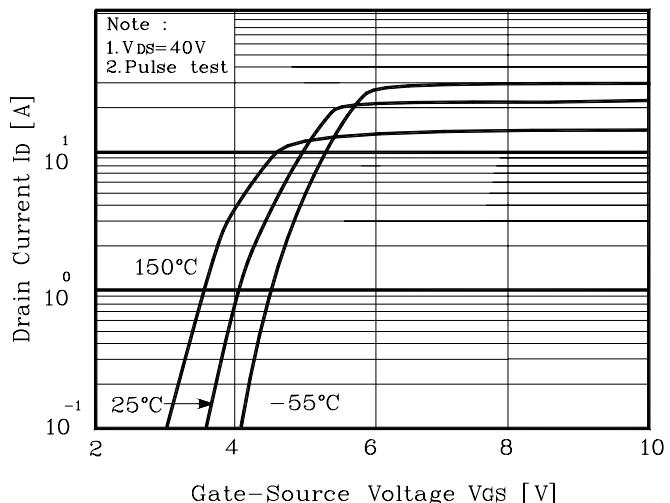


Fig. 3 $R_{DS(on)}$ - I_D

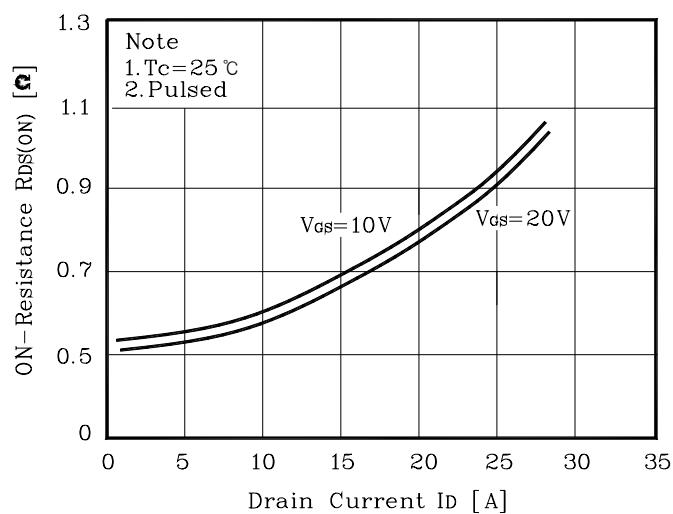


Fig. 4 I_S - V_{SD}

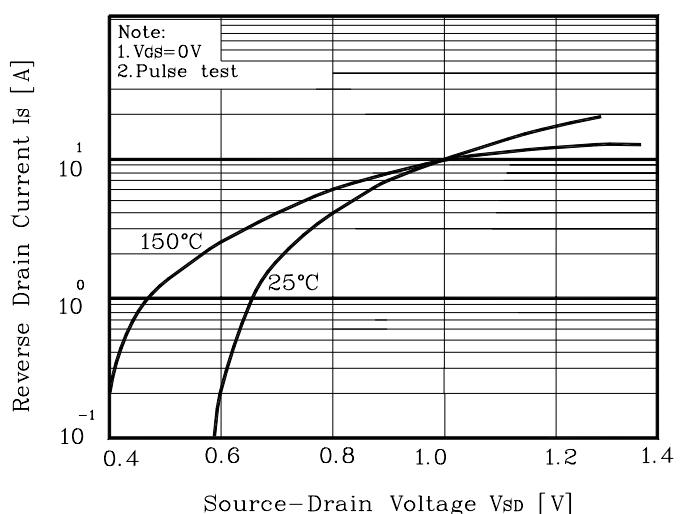


Fig. 5 Capacitance - V_{DS}

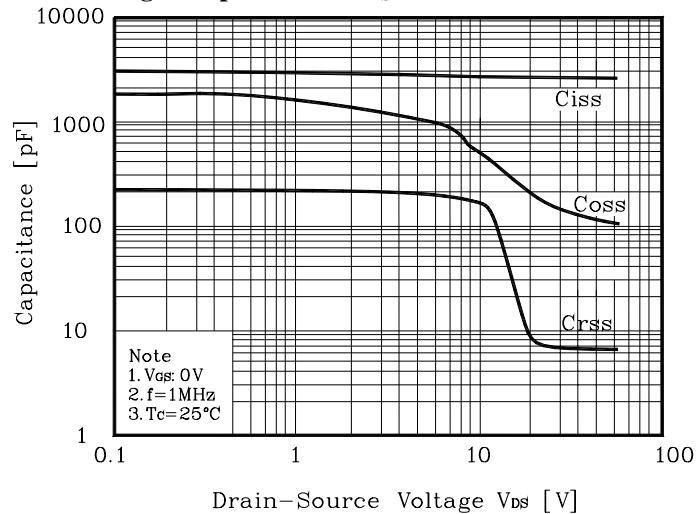
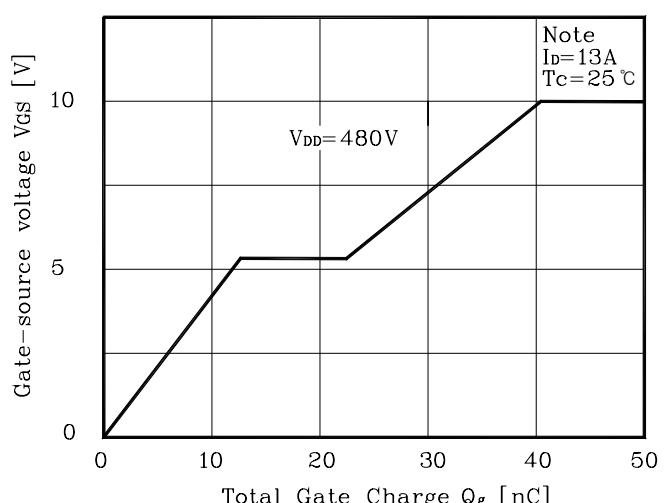


Fig. 6 V_{GS} - Q_g



Electrical Characteristic Curves

Fig. 7 V_{DSS} - T_J

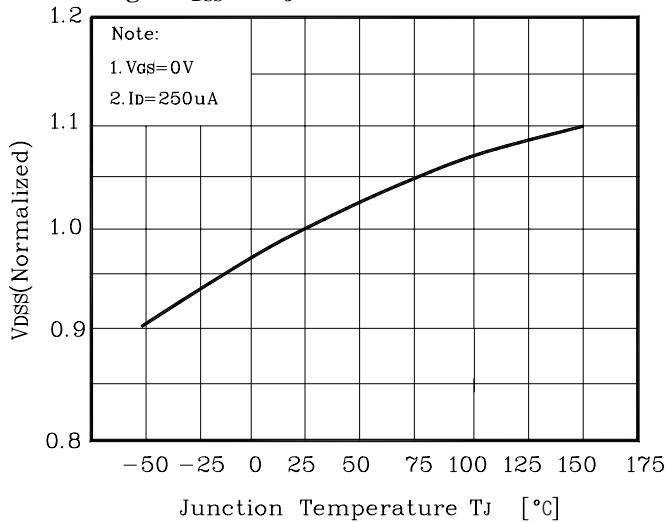


Fig.8 $R_{DS(on)}$ - T_J

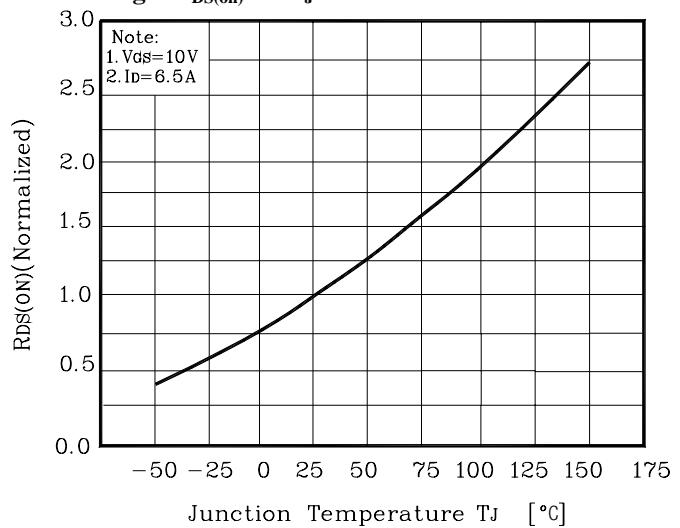


Fig. 9 I_D - T_C

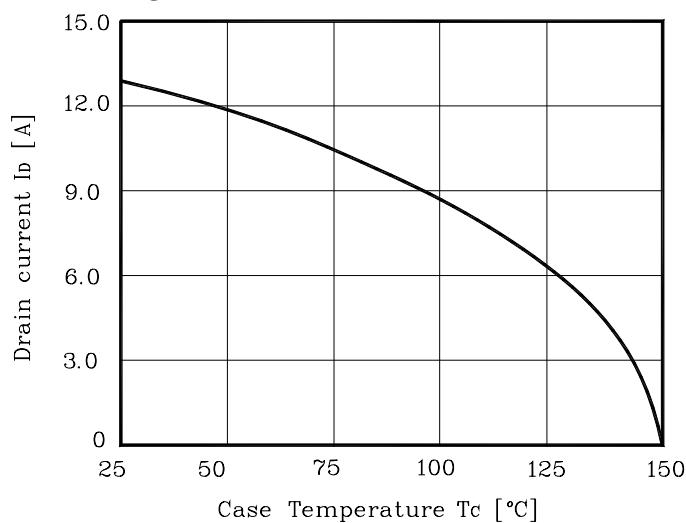


Fig. 10 Safe Operating Area

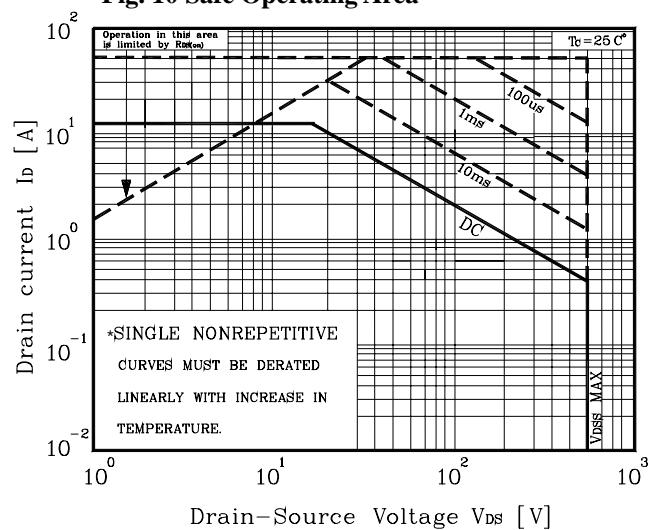


Fig. 11 Gate Charge Test Circuit & Waveform

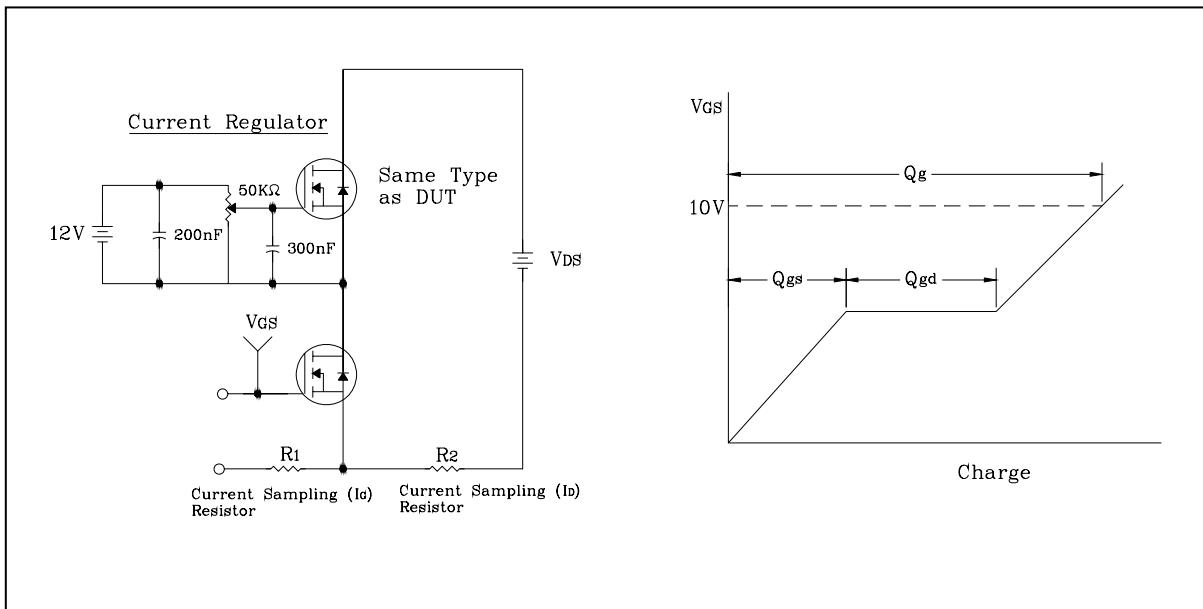


Fig. 12 Resistive Switching Test Circuit & Waveform

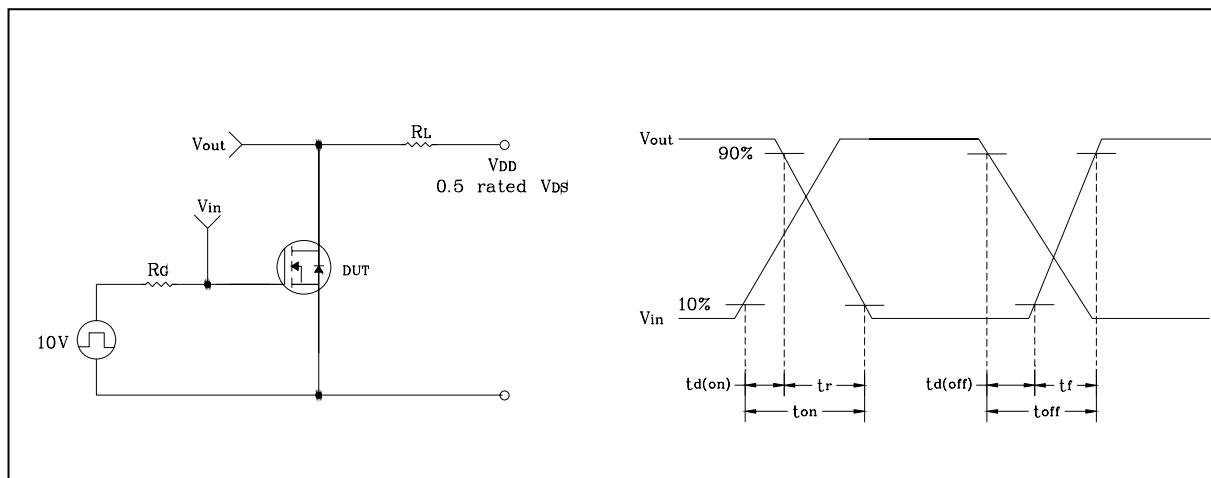


Fig. 13 E_{AS} Test Circuit & Waveform

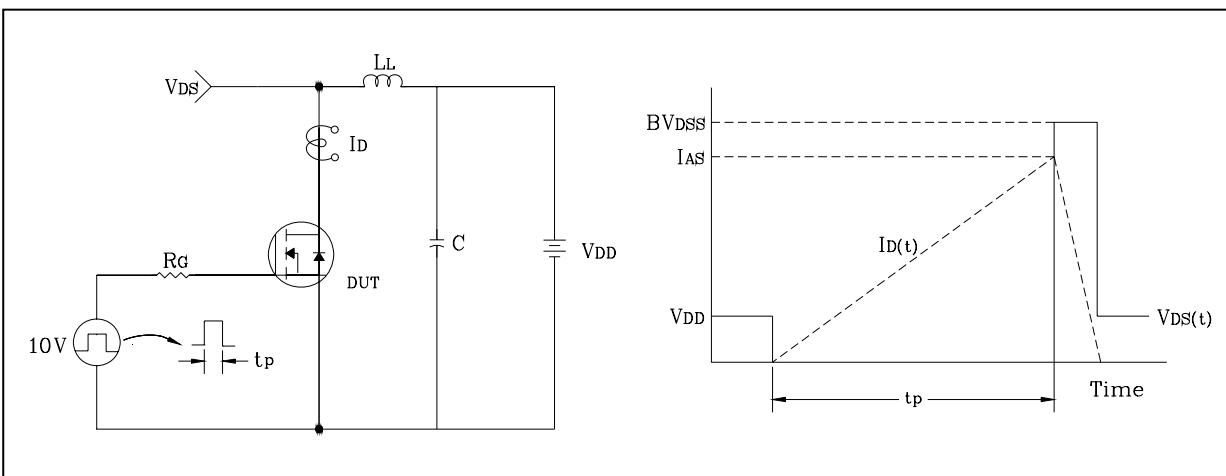
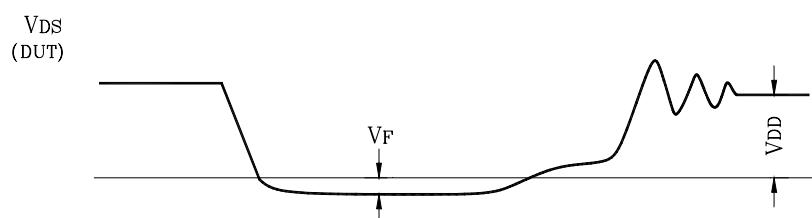
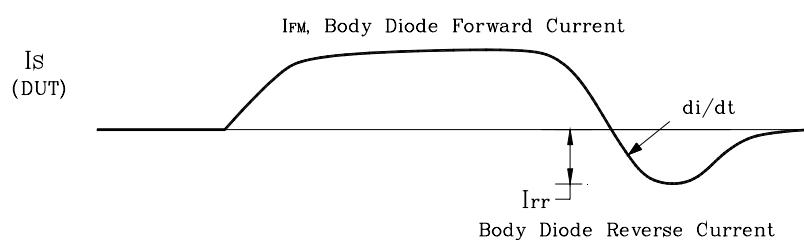
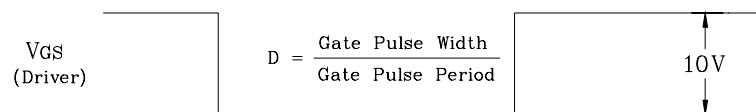
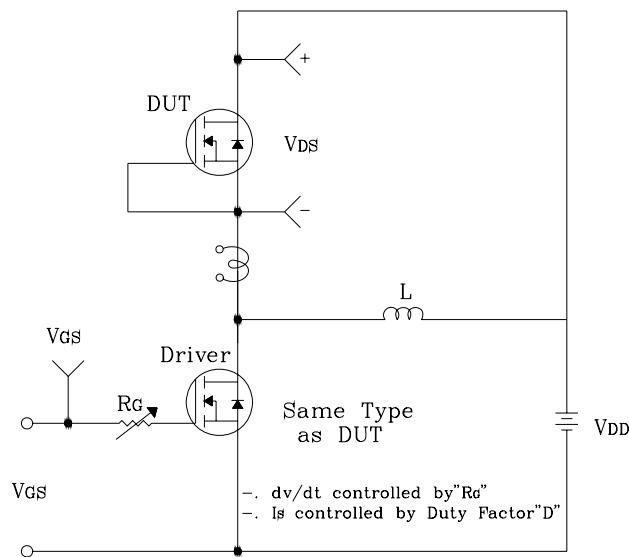
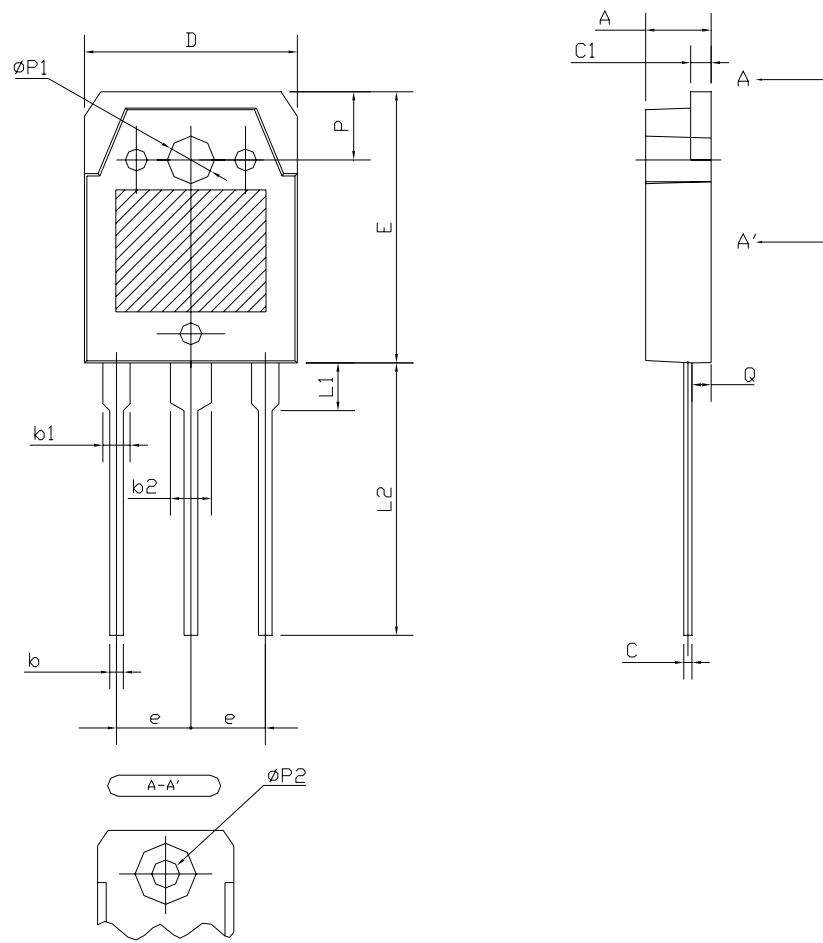


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



Outline Dimension

unit: mm



SYMBOL	MIN	NOM	MAX
A	4.60	4.80	5.00
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
C	0.55	0.60	0.75
C1	1.45	1.50	1.65
D	15.40	15.60	15.80
E	19.70	19.90	20.10
e	5.15	5.45	5.75
L1	3.30	3.50	3.70
L2	19.80	20.00	20.20
P	4.80	5.00	5.20
φP1	3.30	3.40	3.50
φP2	<3.20>		
Q	1.20	1.40	1.60

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